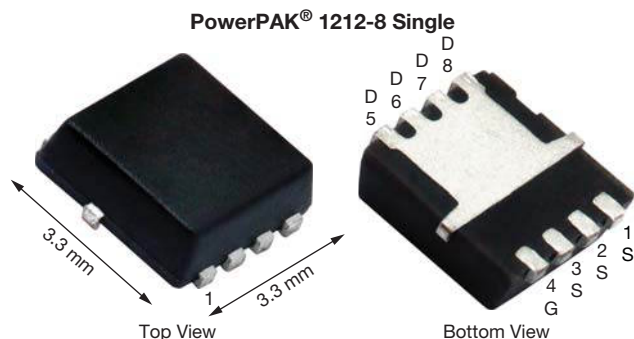


P-Channel 30 V (D-S) MOSFET



PRODUCT SUMMARY	
V_{DS} (V)	-30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V	0.00855
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5$ V	0.01600
Q_g typ. (nC)	30.5
I_D (A)	60 ^{a, g}
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	Si7111EDN-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	-30	V	
Gate-source voltage	V_{GS}	± 12		
Continuous drain current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	60 ^a	A	
	$T_C = 70^\circ\text{C}$	49.3		
	$T_A = 25^\circ\text{C}$	17.4 ^{a, b}		
	$T_A = 70^\circ\text{C}$	13.9 ^{a, b}		
Pulsed drain current ($t = 100 \mu\text{s}$)	I_{DM}	150		
Continuous source-drain diode current	$T_C = 25^\circ\text{C}$	47.3		
	$T_A = 25^\circ\text{C}$	3.7 ^{a, b}		
Single pulse avalanche current	I_{AS}	20		
Single pulse avalanche energy	E_{AS}	20	mJ	
Maximum power dissipation	$T_C = 25^\circ\text{C}$	52	W	
	$T_C = 70^\circ\text{C}$	33.3		
	$T_A = 25^\circ\text{C}$	4.1 ^{a, b}		
	$T_A = 70^\circ\text{C}$	2.6 ^{a, b}		
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$	
Soldering recommendations (peak temperature) ^c		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	R_{thJA}	23	30	$^\circ\text{C}/\text{W}$
Maximum junction-to-case (drain)	R_{thJF}	1.9	2.4	

Notes

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is $81^\circ\text{C}/\text{W}$.
- $T_C = 25^\circ\text{C}$.

FEATURES

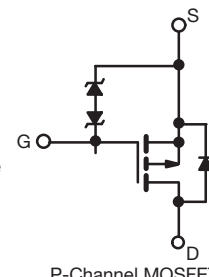
- TrenchFET[®] Gen III p-channel power MOSFET
- $R_{DS(on)}$ rating at $V_{GS} = -2.5$ V
- 100 % R_g and UIS tested
- Typical ESD protection: 4600 V HBM
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Battery switch
- Adapter and charger switch
- Load switch
- Battery management in mobile devices



P-Channel MOSFET

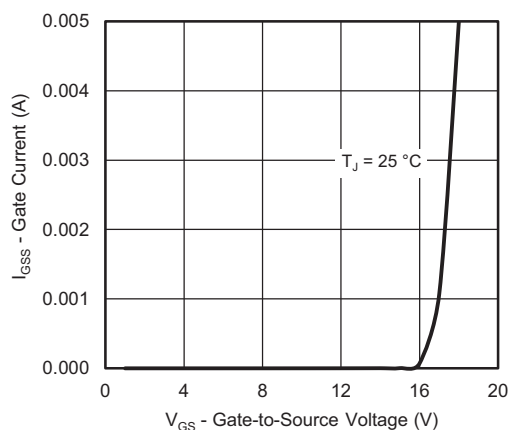
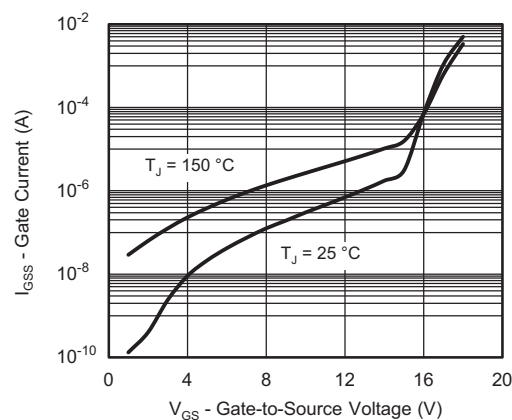
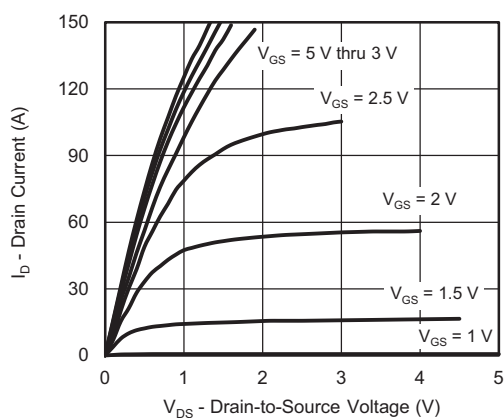
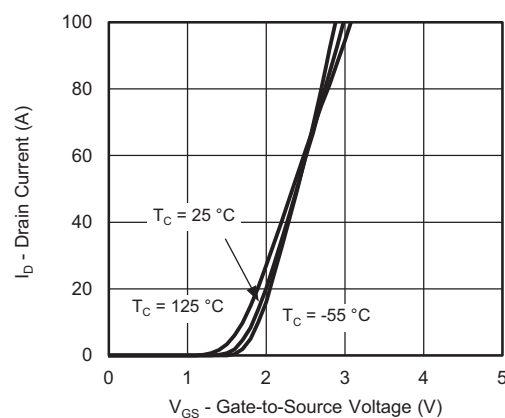
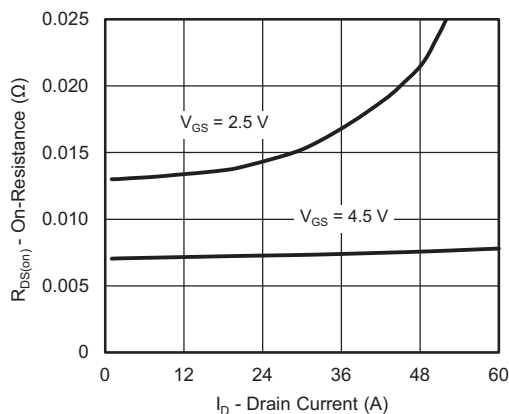
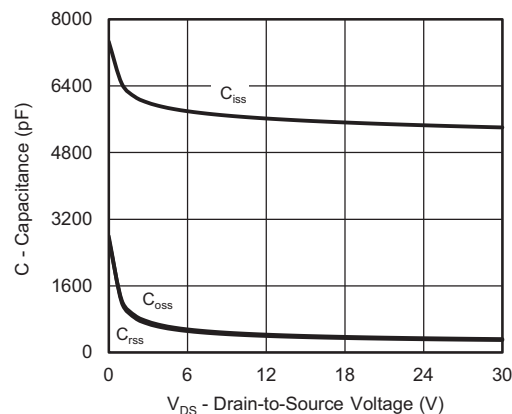


SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-30	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-24	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	3.4	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.6	-	-1.6	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V	-	0.70	10	μA
		V _{DS} = 0 V, V _{GS} = ± 4.5 V	-	0.06	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = -30 V, V _{GS} = 0 V, T _J = 70 °C	-	-	10	
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ -10 V, V _{GS} = -4.5 V	-30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V, I _D = -15 A	-	0.00720	0.00855	Ω
		V _{GS} = -2.5 V, I _D = -10 A	-	0.01310	0.01600	
Forward transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -15 A	-	64	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{DS} = -15 V, V _{GS} = 0 V, f = 1 MHz	-	5860	-	pF
Output capacitance	C _{oss}		-	412	-	
Reverse transfer capacitance	C _{rss}		-	395	-	
C _{rss} /C _{iss} ratio			-	0.068	-	
Total gate charge	Q _g	V _{DS} = -15 V, V _{GS} = -4.5 V, I _D = -10 A	-	56.5	85	nC
		V _{DS} = -15 V, V _{GS} = -2.5 V, I _D = -10 A	-	30.5	46	
Gate-source charge	Q _{gs}		-	9.6	-	
Gate-drain charge	Q _{gd}		-	13.6	-	
Gate resistance	R _g	f = 1 MHz	0.7	3	5.5	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = -15 V, R _L = 1.5 Ω, I _D ≅ -10 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	25	50	ns
Rise time	t _r		-	40	80	
Turn-off delay time	t _{d(off)}		-	120	240	
Fall time	t _f		-	33	66	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	47.3	A
Pulse diode forward current	I _{SM}		-	-	150	
Body diode voltage	V _{SD}	I _S = -5 A, V _{GS} = 0 V	-	-0.75	-1.1	V
Body diode reverse recovery time	t _{rr}	I _F = -10 A, dI/dt = 100 A/μs, T _J = 25 °C	-	32	64	ns
Body diode reverse recovery charge	Q _{rr}		-	30	60	nC
Reverse recovery fall time	t _a		-	16	-	ns
Reverse recovery rise time	t _b		-	16	-	

Notes

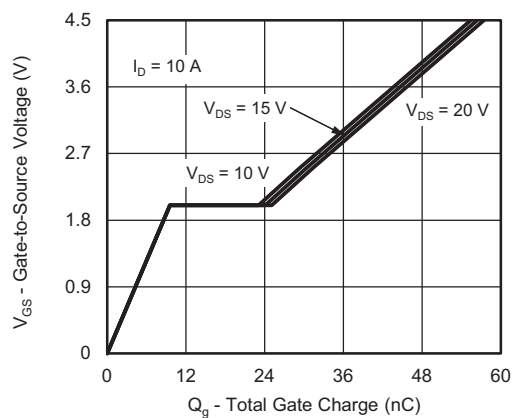
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

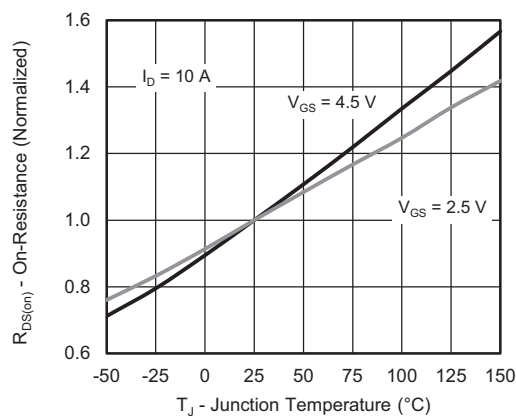
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Gate-Current vs. Gate-Source Voltage

Gate-Current vs. Gate-Source Voltage

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance



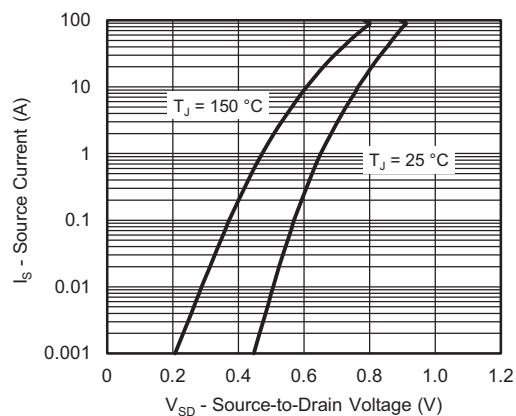
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



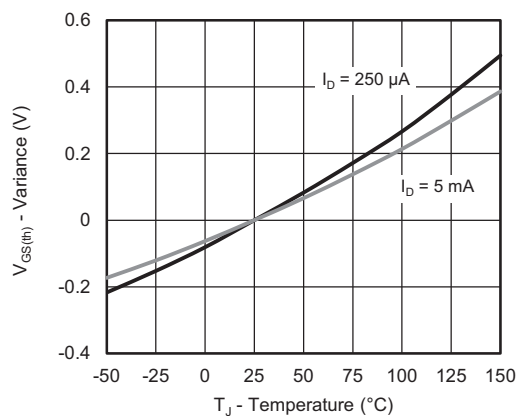
Gate Charge



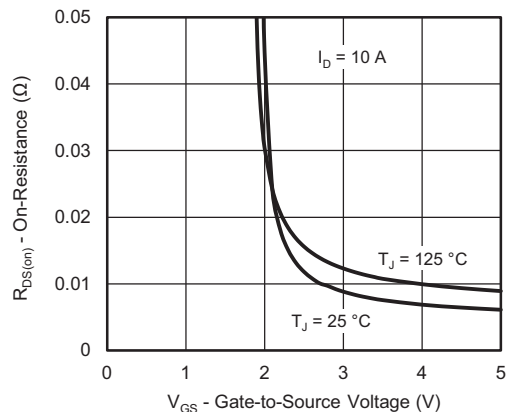
On-Resistance vs. Junction Temperature



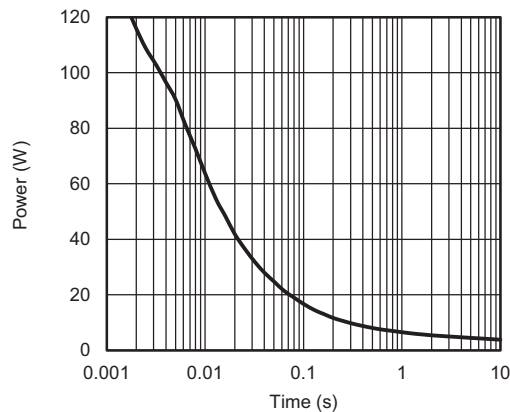
Source-Drain Diode Forward Voltage



Threshold Voltage



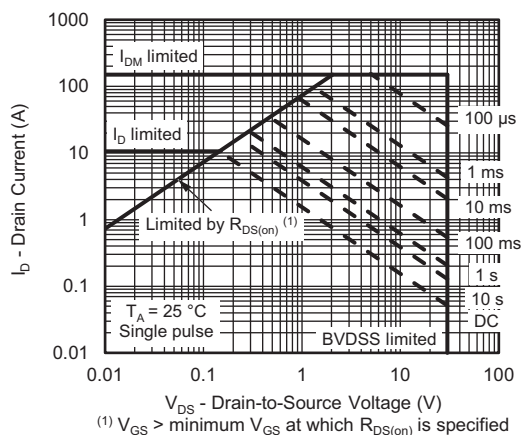
On-Resistance vs. Gate-to-Source Voltage



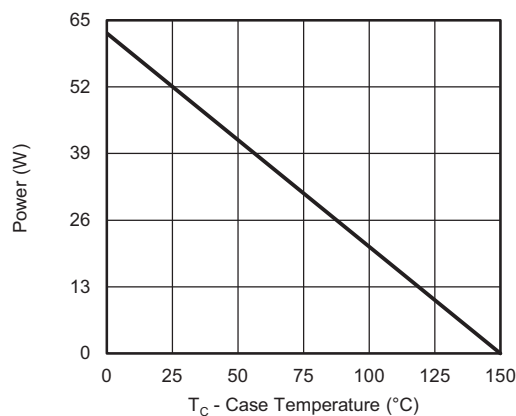
Single Pulse Power, Junction-to-Ambient



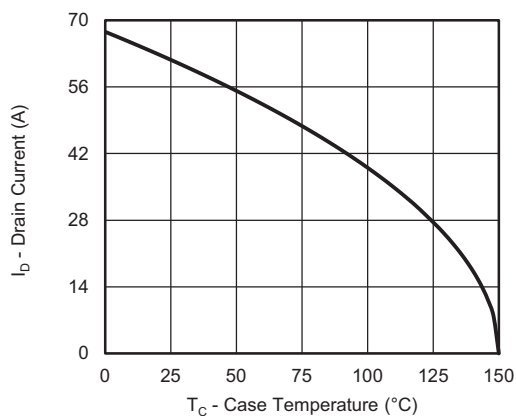
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



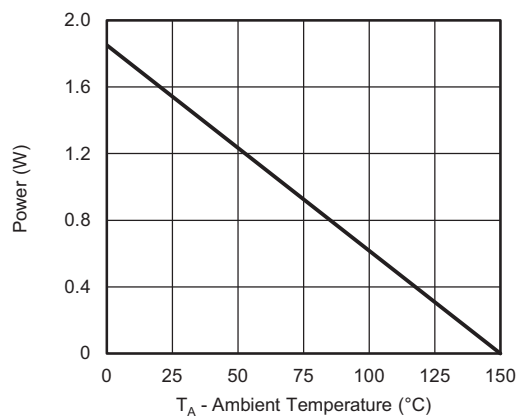
Safe Operating Area, Junction-to-Ambient



Power, Junction-to-Case



Current Derating ^a



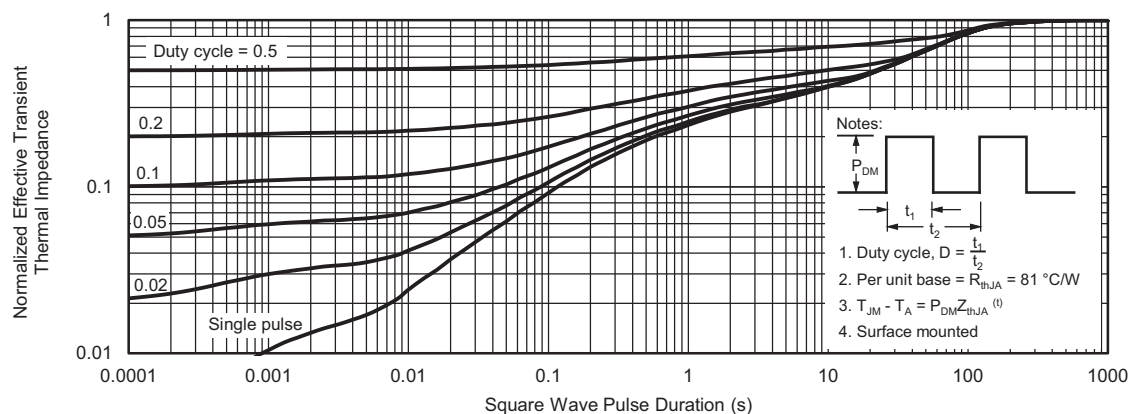
Power, Junction-to-Ambient

Note

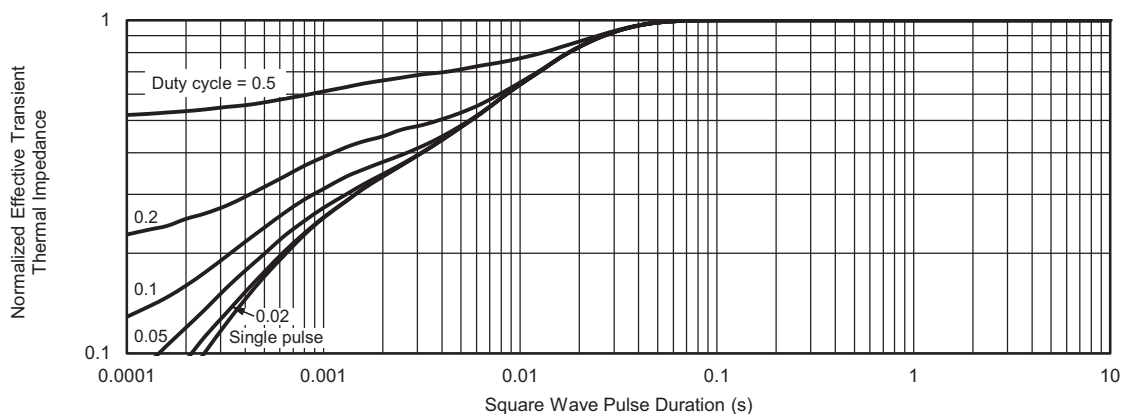
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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